In the claims:

Please amend the claims as follows:

Claim 1 (Currently Amended): A method of fabricating a semiconductor device comprising the steps of:

forming a first crystalline region by irradiating a laser beam to a first region of an amorphous semiconductor film ~~while~~ by relatively moving the laser beam with respect to the first region of said amorphous semiconductor film; and

after fully forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the amorphous semiconductor film including a portion of the first crystalline region ~~of the amorphous semiconductor film formed with the first crystalline region~~ by relatively moving the laser beam with respect to said second region of the amorphous semiconductor film ~~including a portion of the first crystalline region~~;

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm, and the second crystalline region overlaps with the first crystalline region.

Claim 2 (Currently Amended): A method of fabricating a semiconductor device comprising the steps of:

forming a first crystalline region by irradiating a laser beam having a shape at an irradiated face or a vicinity thereof in a linear or a rectangular shape to a first region of an amorphous semiconductor film ~~while~~ by relatively moving the laser beam with respect to the first region of said amorphous semiconductor film; and

after fully forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the amorphous semiconductor film including a portion of the first crystalline region ~~of the amorphous semiconductor film formed with the first crystalline region while~~ by relatively moving the laser beam with respect to said second region of the amorphous semiconductor film ~~including a portion of the first crystalline region~~;

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm, and the second crystalline region overlaps with the first crystalline region.

Claim 3 (Currently Amended): A method of fabricating a semiconductor device comprising the steps of:

forming a first crystalline region by irradiating a laser beam having a shape at an irradiated face or a vicinity thereof in a linear or rectangular shape to a first region of an amorphous semiconductor film ~~while~~ by relatively moving the laser beam in a short direction of the laser beam with respect to said first region of the amorphous semiconductor film; and

after fully forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the amorphous semiconductor film including a portion of the first crystalline region ~~of the amorphous semiconductor film formed with the first crystalline region while~~ by relatively moving the laser beam in the short direction of the laser beam with respect to said second region of the amorphous semiconductor film ~~including a portion of the first crystalline region~~;

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm, and the second crystalline region overlaps with the first crystalline region.

Claim 4 (Currently Amended): A method of fabricating a semiconductor device comprising:

a first step of forming a first crystalline semiconductor film by partially crystallizing an amorphous semiconductor film by a heating treatment; and

a second step of forming a second crystalline semiconductor film by irradiating a laser beam to the crystalline semiconductor film;

wherein the second step comprises the steps of:

forming a first crystalline region by irradiating the laser beam to a first region of the first crystalline semiconductor film ~~while~~ by relatively moving the laser beam with respect to the first region of the first crystalline semiconductor film; and

after fully forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the first crystalline semiconductor film including a portion of the first crystalline region ~~of the first crystalline semiconductor film formed with the first crystalline region while~~ by relatively moving the laser beam with respect to said second region of the first crystalline semiconductor film ~~including a portion of the first crystalline region of the first crystalline semiconductor film~~; and

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm, and the second crystalline region overlaps with the first crystalline region.

Claim 5 (Currently Amended): A method of fabricating a semiconductor device comprising:

a first step of forming a first crystalline semiconductor film by partially crystallizing an amorphous semiconductor film by a heating treatment; and

a second step of forming a second crystalline semiconductor film by irradiating a laser beam having a shape at an irradiated face or a vicinity thereof in a linear or a rectangular shape to the first crystalline semiconductor film;

wherein the second step comprises the steps of:

forming a first crystalline region by irradiating the laser beam to a first region of the first crystalline semiconductor film by relatively moving the laser beam with respect to the first region of the first crystalline semiconductor film; and

after fully forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the first crystalline semiconductor film including a portion of the first crystalline region ~~of the first crystalline semiconductor film formed with the first crystalline region~~ by relatively moving the laser beam with respect to said second region of the first crystalline semiconductor film ~~including a portion of the crystalline region of the first crystalline semiconductor film~~; and

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm, and the second crystalline region overlaps with the first crystalline region.

Claim 6 (Currently Amended): A method of fabricating a semiconductor device comprising:

a first step of forming a first crystalline semiconductor film by partially crystallizing an amorphous semiconductor film by a heating treatment; and

a second step of forming a second crystalline semiconductor film by irradiating a laser beam having a shape at an irradiated face or a vicinity thereof in a linear or a rectangular shape to the first crystalline semiconductor film while relatively moving the laser beam in a short direction of the laser beam with respect to the first crystalline semiconductor film;

wherein the second step comprises the steps of:

forming a first crystalline region by irradiating the laser beam to a first region of the first crystalline semiconductor film ~~while~~ by relatively moving the laser beam in the short direction of the laser beam with respect to the first region of the first crystalline semiconductor film; and

after fully forming the first crystalline region, forming a second crystalline region by irradiating the laser beam to a second region of the first crystalline semiconductor film including

a portion of the first crystalline region ~~of the first crystalline semiconductor film formed with the first crystalline region while~~ by relatively moving the laser beam in the short direction of the laser beam with respect to the second region of the first crystalline semiconductor film ~~including a portion of the first crystalline region of the first crystalline semiconductor film~~; and

wherein:

a wavelength of the laser beam falls in a range of 370 nm through 650 nm, and the second crystalline region overlaps with the first crystalline region.

Claim 7 (Original): The method of fabricating a semiconductor device according to claim 1, wherein a crystalline performance of the first crystalline region, a crystalline performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim 8 (Original): The method of fabricating a semiconductor device according to claim 2, wherein a crystalline performance of the first crystalline region, a crystalline performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim 9 (Original): The method of fabricating a semiconductor device according to claim 3, wherein a crystalline performance of the first crystalline region, a crystalline performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim10 (Original): The method of fabricating a semiconductor device according to claim 4, wherein a crystalline performance of the first crystalline region, a crystalline performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim 11 (Original): The method of fabricating a semiconductor device according to claim 5, wherein a crystalline performance of the first crystalline region, a crystalline performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim 12 (Original): The method of fabricating a semiconductor device according to claim 6, wherein a crystalline performance of the first crystalline region, a crystalline

performance of the second crystalline region and a crystalline performance of a region overlapped with the first crystalline region and the second crystalline region are the same.

Claim 13 (Currently Amended): The method of fabricating a semiconductor ~~apparatus~~ device according to claim 1, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim 14 (Currently Amended): The method of fabricating a semiconductor ~~apparatus~~ device according to claim 2, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim 15 (Currently Amended): The method of fabricating a semiconductor ~~apparatus~~ device according to claim 3, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim 16 (Currently Amended): The method of fabricating a semiconductor ~~apparatus~~ device according to claim 4, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim 17 (Currently Amended): The method of fabricating a semiconductor ~~apparatus~~ device according to claim 5, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim 18 (Currently Amended): The method of fabricating a semiconductor ~~apparatus~~ device according to claim 6, wherein the semiconductor device is a liquid crystal display apparatus or an EL display apparatus.

Claim19 (Currently Amended): The method of fabricating a semiconductor device according to claim 1, wherein the semiconductor device is employed on a device selected from the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 20 (Currently Amended): The method of fabricating a semiconductor device according to claim 2, wherein the semiconductor device is employed on a device selected from

the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 21 (Currently Amended): The method of fabricating a semiconductor device according to claim 3, wherein the semiconductor device is employed on a device selected from the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 22 (Currently Amended): The method of fabricating a semiconductor device according to claim 4, wherein the semiconductor device is employed on a device selected from the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 23 (Currently Amended): The method of fabricating a semiconductor device according to claim 5, wherein the semiconductor device is employed on a device selected from the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 24 (Currently Amended): The method of fabricating a semiconductor device according to claim 6, wherein the semiconductor device is employed on a device selected from the group consisting of: a portable telephone, a video camera, a digital camera, a projector, a goggle type display, a personal computer, a DVD player, an electronic book and a portable information terminal.

Claim 25 (Original): The method of fabricating a semiconductor device according to claim 1, wherein said laser beam is a laser beam selected from the group consisting of: a second harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.

Claim 26 (Original): The method of fabricating a semiconductor device according to claim 2, wherein said laser beam is a laser beam selected from the group consisting of: a second

harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.

Claim 27 (Original): The method of fabricating a semiconductor device according to claim 3, wherein said laser beam is a laser beam selected from the group consisting of: a second harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.

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Claim 28 (Original): The method of fabricating a semiconductor device according to claim 4, wherein said laser beam is a laser beam selected from the group consisting of: a second harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.

Claim 29 (Original): The method of fabricating a semiconductor device according to claim 5, wherein said laser beam is a laser beam selected from the group consisting of: a second harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.

Claim 30 (Original): The method of fabricating a semiconductor device according to claim 6, wherein said laser beam is a laser beam selected from the group consisting of: a second harmonic of a YAG laser, a second harmonic of a YVO_4 laser and a second harmonic of a YLF laser.

In the abstract:

Please replace the abstract with the following:

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A semiconductor device is fabricated by forming a first crystalline region by irradiating a laser beam to a first region of an amorphous semiconductor film by relatively moving the laser beam with respect to the first region of the amorphous semiconductor film. A second crystalline region is formed by irradiating the laser beam to a second region of the amorphous semiconductor film including a portion of the first crystalline region by relatively moving the laser beam with respect to the second region of the amorphous semiconductor film. The wavelength of the laser beam falls in a range of 370 nm through 650 nm. In general, crystalline performance of the first crystalline region, the second crystalline region, and a region of overlap between the first crystalline region and the second crystalline region are the same.